



#### SI2309DS-T1-E3 Information

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For Reference Only

**Part Number** SI2309DS-T1-E3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET P-CH 60V 1.25A SOT23-3

**Package** TO-236-3, SC-59, SOT-23-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## SI2309DS-T1-E3 Specifications

Manufacturer Part Number         SI2309DS-T1-E3           Manufacturer         Vishay Siliconix           Category         Discrete Semiconductor Products		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-236-3, SC-59, SOT-23-3           Series         TrenchFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         -           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         1V @ 250µA (Min)           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.25W (Ta)           Rds On (Max) @ Id, Vgs         340 mOhm @ 1.25A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3	Manufacturer Part Number	SI2309DS-T1-E3
Package         TO-236-3, SC-59, SOT-23-3           Series         TrenchFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         -           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         1V @ 250μA (Min)           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.25W (Ta)           Rds On (Max) @ Id, Vgs         340 mOhm @ 1.25A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3	Manufacturer	Vishay Siliconix
Package         TO-236-3, SC-59, SOT-23-3           Series         TrenchFET?           FET Type         P-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         -           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         1V @ 250μA (Min)           Gate Charge (Qg) (Max) @ Vgs         12nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         -           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         1.25W (Ta)           Rds On (Max) @ Id, Vgs         340 mOhm @ 1.25A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         SOT-23-3 (TO-236)           Package / Case         TO-236-3, SC-59, SOT-23-3	Category	Discrete Semiconductor Products
SeriesTrenchFET?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.25W (Ta)Rds On (Max) @ Id, Vgs340 mOhm @ 1.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250µA (Min) Gate Charge (Qg) (Max) @ Vgs 12nC @ 10V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.25W (Ta) Rds On (Max) @ Id, Vgs 340 mOhm @ 1.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case Totology (Max) (Mound Source Administration of Carlot)  Power Dissipation (Max) 1.25W (Ta)	Package	TO-236-3, SC-59, SOT-23-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  - Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  MOSFET (Metal Oxide)  60V  - Vg  Wost  1	Series	TrenchFET?
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.25W (Ta)Rds On (Max) @ Id, Vgs340 mOhm @ 1.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  1V @ 250µA (Min)  Gate Charge (Qg) (Max) @ Vgs  12nC @ 10V  Input Capacitance (Ciss) (Max) @ Vds  - Vgs (Max)  #20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  340 mOhm @ 1.25A, 10V  Operating Temperature  Supplier Device Package  Package / Case  - Current - Continuous Drain (Id) @ 25°C	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs12nC @ 10VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.25W (Ta)Rds On (Max) @ Id, Vgs340 mOhm @ 1.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id       1V @ 250μA (Min)         Gate Charge (Qg) (Max) @ Vgs       12nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       -         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       1.25W (Ta)         Rds On (Max) @ Id, Vgs       340 mOhm @ 1.25A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Surface Mount         Supplier Device Package       SOT-23-3 (TO-236)         Package / Case       TO-236-3, SC-59, SOT-23-3	Current - Continuous Drain (Id) @ 25°C	-
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  - Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Jupit Capacitance (Ciss) (Max) @ Id, Vgs  Ado mohm @ 1.25A, 10V  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-23-3 (TO-236)  Package / Case  TO-236-3, SC-59, SOT-23-3	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max) ±20V  FET Feature -  Power Dissipation (Max) 1.25W (Ta)  Rds On (Max) @ Id, Vgs 340 mOhm @ 1.25A, 10V  Operating Temperature -55°C ~ 150°C (TJ)  Mounting Type Surface Mount  Supplier Device Package SOT-23-3 (TO-236)  Package / Case TO-236-3, SC-59, SOT-23-3	Vgs(th) (Max) @ Id	1V @ 250μA (Min)
Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.25W (Ta)Rds On (Max) @ Id, Vgs340 mOhm @ 1.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	Gate Charge (Qg) (Max) @ Vgs	12nC @ 10V
FET Feature - Power Dissipation (Max) 1.25W (Ta) Rds On (Max) @ Id, Vgs 340 mOhm @ 1.25A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Input Capacitance (Ciss) (Max) @ Vds	-
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-23-3 (TO-236)  Package / Case  1.25W (Ta)  340 mOhm @ 1.25A, 10V  Surface Mount  Surface Mount  TO-236-3, SC-59, SOT-23-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs340 mOhm @ 1.25A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageSOT-23-3 (TO-236)Package / CaseTO-236-3, SC-59, SOT-23-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  SOT-23-3 (TO-236)  Package / Case  TO-236-3, SC-59, SOT-23-3	Power Dissipation (Max)	1.25W (Ta)
Mounting Type Surface Mount Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Rds On (Max) @ Id, Vgs	340 mOhm @ 1.25A, 10V
Supplier Device Package SOT-23-3 (TO-236) Package / Case TO-236-3, SC-59, SOT-23-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-236-3, SC-59, SOT-23-3	Mounting Type	Surface Mount
	Supplier Device Package	SOT-23-3 (TO-236)
Report errors?	Package / Case	TO-236-3, SC-59, SOT-23-3
		Report errors?

#### SI2309DS-T1-E3 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## SI2309DS-T1-E3 Payment Methods





















## SI2309DS-T1-E3 Shipping Methods













If you have any question about SI2309DS-T1-E3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com